Unit: mm

2.5±0.1 (0.8)

0.45+0.10

1:Emitter 2:Collector

MT-2-A1 Package

(HW type)

3:Base

1.05±0.05

5±0.5

0.7

0.65 max.

0.45+0.1

2.5

Note: In addition to the

lead type shown in the upper figure, the

type as shown in

the lower figure is also available.

1.2±0.1

 $0.45^{+0}_{-0}$ 

# 2SC4391

### Silicon NPN epitaxial planer type

For low-frequency output amplification Complementary to 2SA1674

#### Features

- Low collector to emitter saturation voltage V<sub>CE(sat)</sub>.
- High collector to emitter voltage V<sub>CEO</sub>.
- Allowing supply with the radial taping.

9 × /					
Parameter	Symbol	Ratings	Unit		
Collector to base voltage	V <sub>CBO</sub>	80	V		
Collector to emitter voltage	V <sub>CEO</sub>	80	V		
Emitter to base voltage	V <sub>EBO</sub>	5	V		
Peak collector current	I <sub>CP</sub>	1.5	А		
Collector current	I <sub>C</sub>	1	А		
Collector power dissipation	$P_{C}^{*}$	1	W		
Junction temperature	Tj	150	°C		
Storage temperature	T <sub>stg</sub>	-55 ~ +150	°C		

#### Absolute Maximum Ratings (Ta=25°C)

\* Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion

#### Electrical Characteristics (Ta=25°C)

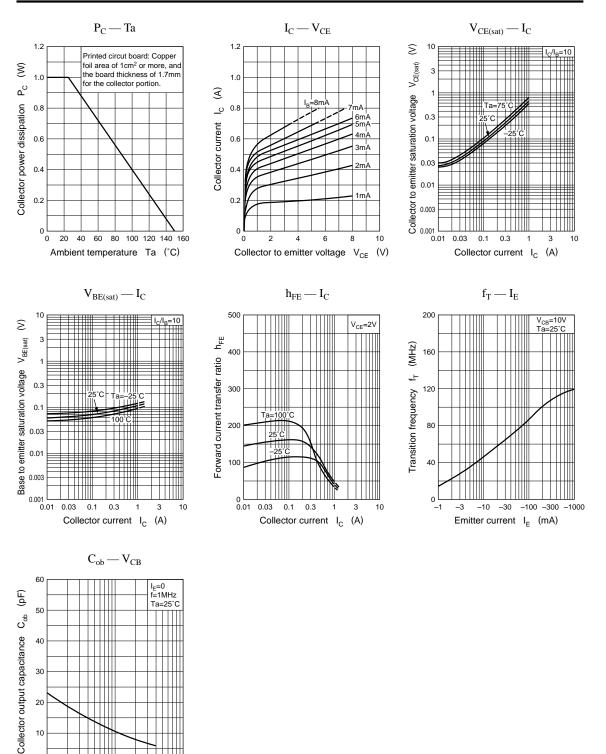
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 40V, I_E = 0$			0.1	μΑ
Collector to base voltage	V <sub>CBO</sub>	$I_C = 10\mu A, I_E = 0$	80			V
Collector to emitter voltage	V <sub>CEO</sub>	$I_C = 1 \text{mA}, I_B = 0$	80			V
Emitter to base voltage	V <sub>EBO</sub>	$I_{\rm E} = 10 \mu A, I_{\rm C} = 0$	5			V
Forward current transfer ratio	h <sub>FE1</sub> *1	$V_{CE} = 2V, I_{C} = 100mA$	120		340	
	h <sub>FE2</sub>	$V_{CE} = 2V, I_C = 500mA^{*2}$	60			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}^{*2}$		0.15	0.3	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = 500 {\rm mA}, I_{\rm B} = 50 {\rm mA}^{*2}$		0.85	1.2	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10V, I_E = -50mA, f = 200MHz$		120		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 10V, I_E = 0, f = 1MHz$		10	20	pF

\*2 Pulse measurement

\*1hFE1 Rank classification

Rank	R	S
h <sub>FE1</sub>	120 ~ 240	170 ~ 340

#### Transistor



20

10

0∟ 1

3

30

100

10

Collector to base voltage  $V_{CB}$  (V)

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